

Advanced Compact MOSFET Models

Introduction

MOSFET modeling is moving away from a source-referenced, threshold voltage based formulation

The two main approaches for advanced MOSFET compact models are:

- **charge based models**
- **surface potential based models**

The joint paper and Forum and Panel are intended to disseminate information on the history and technical details of these approaches

Presentation of Joint Paper

Advanced Compact Models for MOSFETs

Forum Goals:

Provide detailed presentations, by model developers, of the pros and cons of the two approaches to advanced MOSFET modeling

Disseminate basic information about, and provide education on, the two new approaches to MOSFET modeling to modeling and characterization engineers in industry

Forum

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